Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series B" triac is designed to commutate the full RMS current at the maximum junction temperature without the aid of a snubber.

2. Features and benefits

- 3Q technology for improved noise immunity
- · High commutation capability with maximum false trigger immunity
- High voltage capability
- Less sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- · General purpose motor control
- · Small loads in washing machines
- Solenoid drivers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54$ °C; Fig. 1; Fig. 2; Fig. 3	-	-	1	Α
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	5	-	50	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2——T1
2	G	gate		sym051
3	T1	main terminal 1	TO-92 (SOT54)	symoon

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA201-600B	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	1	Α
I _{TSM}	non-repetitive peak on-	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.8 \text{ms}$	-	13.7	Α
	state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5	-	12.5	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I_{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
Tj	junction temperature		-40	125	°C

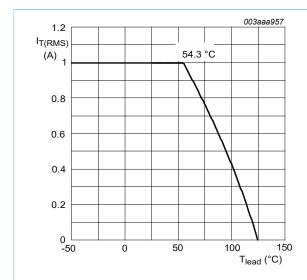


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

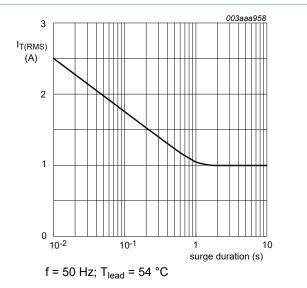


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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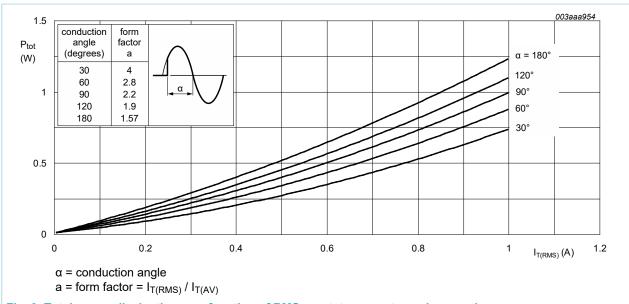


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

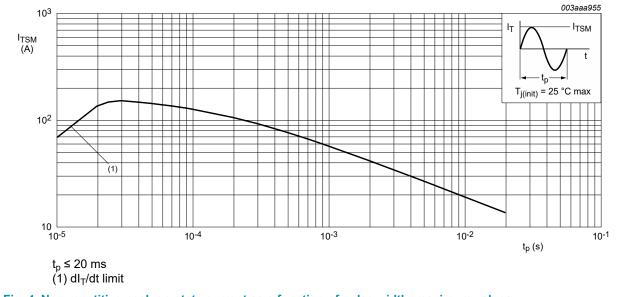


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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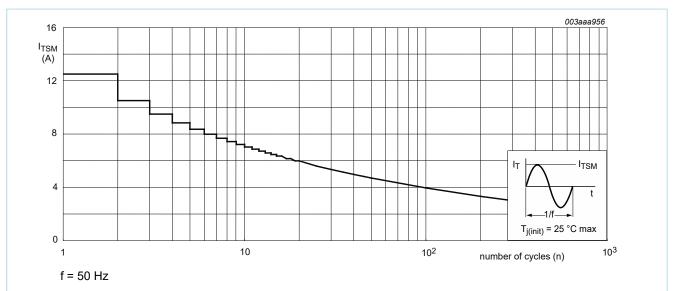


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

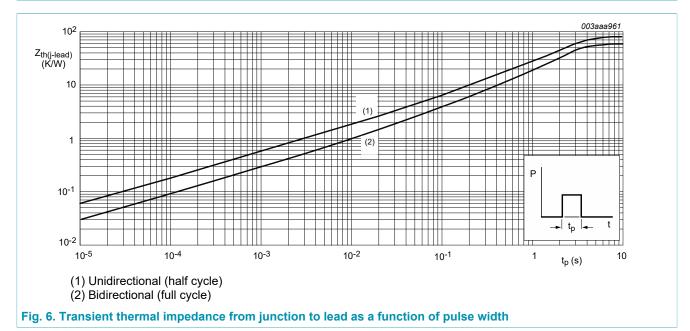
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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; Fig. 6	-	_	60	K/W
		half cycle; Fig. 6	-	_	80	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; lead length = 4 mm	-	150	-	K/W



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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	5	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	5	-	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	50	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		'			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/s; (snubberless condition); gate open circuit	12	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	16	-	-	A/ms

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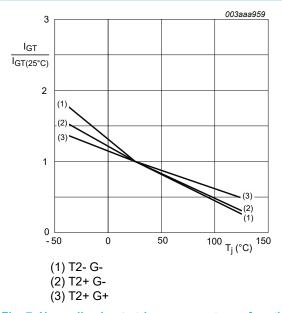


Fig. 7. Normalized gate trigger current as a function of junction temperature

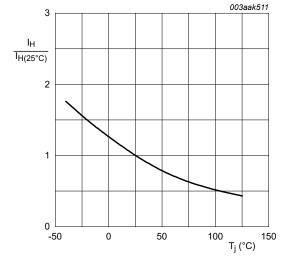


Fig. 9. Normalized holding current as a function of junction temperature

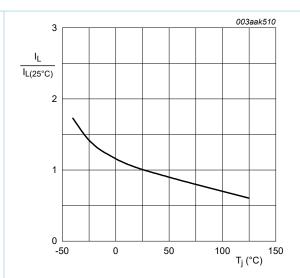
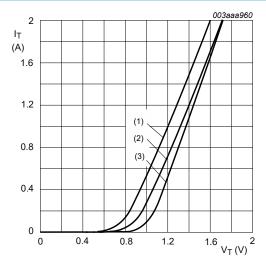


Fig. 8. Normalized latching current as a function of junction temperature



 $\begin{array}{l} \text{V}_{\text{o}} = 1.02 \text{ V}; \text{ R}_{\text{s}} = 0.358 \ \Omega \\ \text{(1)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ typical values} \\ \text{(2)} \text{ T}_{\text{j}} = 125 \ ^{\circ}\text{C}; \text{ maximum values} \\ \text{(3)} \text{ T}_{\text{j}} = 25 \ ^{\circ}\text{C}; \text{ maximum values} \end{array}$

Fig. 10. On-state current as a function of on-state voltage

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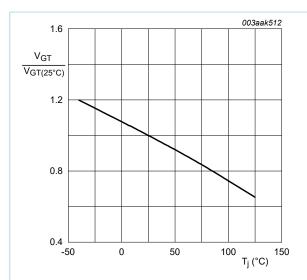


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

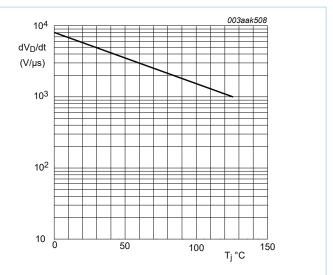
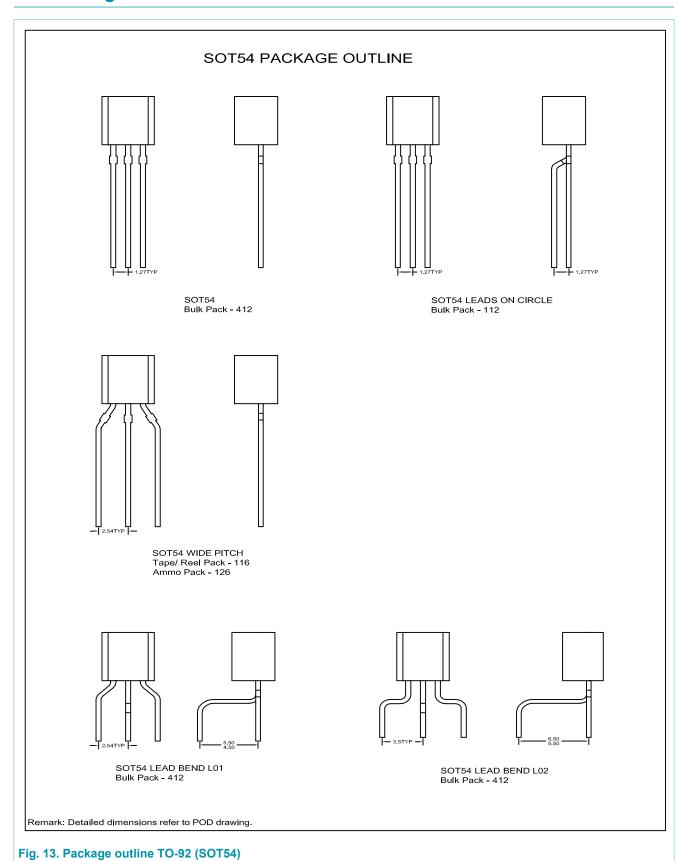


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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